

AMENDMENT TO THE CLAIMS:

Please amend the claims as follows:

1.- 12. (Canceled)

13. (Previously Presented) A vapor reaction method comprising the steps of:
providing a pair of first and second electrodes within a reaction chamber, said pair of electrodes being arranged substantially in parallel with each other;

placing a substrate in the reaction chamber on said first electrode so that a first surface of said substrate faces toward said second electrode;

introducing a first film forming gas into said reaction chamber through said second electrode;

exciting said first film forming gas in order to form a first insulating film by first vapor deposition on said substrate placed in said reaction chamber;

introducing a second film forming gas into said reaction chamber through said second electrode;

exciting said second film forming gas in order to form a second insulating film by a second vapor deposition on said first insulating film in said reaction chamber wherein said first and second insulating films contact each other;

removing said substrate from said reaction chamber after the formation of the first and second insulating films;

introducing a cleaning gas comprising nitrogen fluoride into said reaction chamber through said second electrode;

exciting said cleaning gas in order to remove unnecessary layers caused the first and second vapor depositions from an inside of the reaction chamber,

wherein one of the first and second insulating films comprises silicon nitride and the other one of the first and second insulating films comprises a different material from said one of the first and second insulating films.

14. – 15. (Canceled)

16. (Previously Presented) A vapor reaction method comprising the steps of:
providing a pair of first and second electrodes within a reaction chamber, said pair of electrodes being arranged, substantially in parallel with each other;

placing a substrate in a reaction chamber on said first electrode so that a first surface of said substrate faces toward said second electrode;

introducing a first film forming gas into said reaction chamber through said second electrode;

exciting said first film forming gas in order to form a first film comprising SiO_2 by vapor deposition on said substrate placed in said reaction chamber;

introducing a second film forming gas into said reaction chamber through said second electrode;

exciting said second film forming gas in order to form a second film comprising silicon nitride by vapor deposition on said first film in said reaction chamber;

removing said substrate from said reaction chamber after the formation of the first and second films;

introducing a cleaning gas comprising nitrogen fluoride into said reaction chamber through said second electrode;

exciting said cleaning gas in order to perform a cleaning to remove unnecessary layers deposited on an inside of the reaction chamber due to the formation of the first and second films.

17. (Previously Presented) A vapor reaction method comprising the steps of:
providing a pair of first and second electrodes within a reaction chamber, said pair of electrodes being arranged substantially in parallel with each other;

placing a substrate in a reaction chamber on said first electrode so that a first surface of said substrate faces toward said second electrode;

introducing a first film forming gas into said reaction chamber through said second electrode;

exciting said first film forming gas in order to form a first film comprising silicon nitride by vapor deposition on said substrate placed in said reaction chamber;

introducing a second film forming gas into said reaction chamber through said second electrode;

exciting said second film forming gas in order to form a second film by vapor deposition by vapor deposition directly on said first film in said reaction chamber;

removing said substrate from said reaction chamber after the formation of the first and second films;

introducing a cleaning gas comprising nitrogen fluoride into said reaction chamber through said second electrode;

exciting said cleaning gas in order to remove unnecessary layers formed on an inside of the reaction chamber due to the formation of the first and second films.

18. - 19. (Canceled)

20. (Currently Amended) The method of claims [[3, 6, 9, 11,]] 13, 16, 17 or 18 wherein said cleaning gas comprises nitrogen fluoride.

21. (Previously Presented) A method of fabricating electronic devices comprising the steps of:

providing a pair of electrodes within a reaction chamber wherein said pair of electrodes are opposed in parallel with each other;

placing a substrate in a reaction chamber wherein said substrate is held by one of said electrodes;

introducing a first film forming gas into said reaction chamber through the other one of said electrodes;

exciting said first film forming gas to form a first film by first chemical vapor

deposition on said substrate;

introducing a second film forming gas into said reaction chamber through the other one of said electrodes;

exciting said second film forming gas to form a second film by second chemical vapor deposition on said first film, said second film comprising a different material from said first film;

removing said substrate from said reaction chamber after the formation of said first and second films;

introducing a cleaning gas into said reaction chamber through said other one of the electrodes; and

conducting a cleaning of an inside of said reaction chamber by using said cleaning gas to remove layers caused by at least said first and second vapor phase deposition,

wherein one of the first and second films comprises silicon nitride.

22. (Previously Presented) A method according to claim 21 wherein said first chemical vapor deposition is a photo CVD.

23. (Previously Presented) A method according to claim 21 wherein said second chemical vapor deposition is a plasma CVD.

24. (Previously Presented) A method according to claim 21 wherein said cleaning gas is excited by said pair of electrodes.

25. (Previously Presented) A method according to claim 21 wherein said other one of the electrodes is provided with a plurality of ports for introducing said cleaning gas into the reaction chamber.

26. (Previously Presented) A method of fabricating electronic devices comprising the steps of:

providing a pair of electrodes within a reaction chamber wherein said pair of electrodes are opposed in parallel with each other;

placing a substrate in a reaction chamber wherein said substrate is held by one of said electrodes;

introducing a first film forming gas into said reaction chamber through the other one of said electrodes;

exciting said first film forming gas to form a first film by first chemical vapor deposition on said substrate;

introducing a second film forming gas into said reaction chamber through the other one of said electrodes;

exciting said second film forming gas to form a second film by second chemical vapor deposition on said first film wherein said second film comprises a different material from said first film;

removing said substrate from said reaction chamber after the formation of said first and second films;

introducing a cleaning gas into said reaction chamber through said other one of the electrodes; and

conducting a cleaning of an inside of said reaction chamber by using said cleaning gas to remove layers caused by at least first and second vapor phase deposition,

wherein one of the first and second films comprises silicon nitride.

27. (Previously Presented) A method according to claim 26 wherein said first chemical vapor deposition is a photo CVD.

28. (Previously Presented) A method according to claim 26 wherein said second chemical vapor deposition is a plasma CVD.

29. (Previously Presented) A method according to claim 26 wherein said cleaning gas is excited by said pair of electrodes.

30. (Previously Presented) A method according to claim 26 wherein said other one of the electrodes is provided with a plurality of ports for introducing said cleaning gas into the reaction chamber.